Core level quasiparticles: Photon-created quasiholes in epitaxial silicene

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Studies of creation of core holes and the induced correlations in solids are important for understanding their constituent atoms, chemical environment, electronic states, and various physical properties. Owing to the complicated many-body interaction, it is still a challenge to tackle the renormalization of the bare hole. We follow the content of density functional theory (DFT) to study the core-level quasiparticles in silicene on the $ZrB_2(0001)$ surface. The energies and involved charge density of the renormalized holes are calculated. The absolute binding energies including the splitting due to spin-orbit coupling are compared to the observed spectra by high-resolution X-ray photoelectron spectroscopy (XPS). The good agreement advocates the success of DFT in describing many-body interactions at the surface and resolves the puzzling discrepancy between the observed XPS results and the Kohn-Sham eigenvalues of planar-like silicene on $ZrB_2(0001)$.

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The total energy and charge density (CD) of a many-body system have been demonstrated to be describable via a set of non-interacting Kohn-Sham orbitals in the framework of density functional theory (DFT)[1, 2]. The DFT has been shown to successfully predict the ground-state properties by knowing the atomic constituents of a system and continued as one of the state-of-the-art methods in studying condensed matter[3]. The physical meaning of Kohn-Sham orbitals other than the mapping of their CD to the many-body CD is still under discussion[4–6]. Although the highest occupied orbital of a system has been proven to deliver the ionization energy[7, 8] and each eigenvalue of Kohn-Sham orbital is widely accepted to yield the derivative of the total energy with respect to its occupation[9], it is well known that the eigenvalues cannot be directly used to compare with the quasiparticle energies[6, 10, 11] that are measured in photoelectron spectra[12–14]. This makes sense since creation or annihilation of a single-particle eigenstate in an interacting many-body system must cause strong or weak but non-zero correlation, and the involved degrees of freedom in the many-body multiplets must be much larger than the number of single-particle eigenstates in general.

Two-dimensional materials are promising for the next generation of technology and have been extensively studied[15–23]. Among them, researches on silicene have caught great attention since its successful fabrication on metallic substrates[17–23]. Recent formation of isolated quasi-freestanding silicene showing the feature of massless Dirac fermions further remarked a big progress[24]. As expected, DFT has provided substantial supports for understanding silicene[17–24]. In the case of silicene on $ZrB_2(0001)$[23], the DFT-proposed ground state, the planar-like silicene[25], can well reproduce the valence band structure measured by the angle-resolved photoelectron spectroscopy via the interpretation of Kohn-Sham eigenvalues as quasiparticle energies[26]. However, the core-level X-ray photoelectron spectroscopy (XPS)[12, 13] spectrum of silicene on $ZrB_2(0001)$ was found to be consistent with the density of states of Kohn-Sham orbitals (DOS) of a buckled-like structure, not the planar-like one[23]. This is puzzling and implies that the physics underlying the core-level XPS spectrum is beyond what the DOS can offer, indicating a need of direct theoretical access of accurate energies of quasiparticles.

Accurately accounting for the screening behavior of electrons to the photon-created hole is a difficult task.[27–32]. The DFT calculation of total energy difference between N and $N-1$ electrons of a system beyond perturbation approaches[10, 11] confronts the periodic images of the hole due to the commonly imposed periodic boundary condition and therefore cannot reflect the nature of the "$N-1$"-electron solid state. Nevertheless, this difficulty has recently been overcome by an exact Coulomb-cutoff technique[33, 34]. The designated core hole can also be introduced by adding a penalty functional. It is then interesting to revisit the picture of quasiparticles using the newly developed methods[34] with considering the effects of exchange and correlation triggered by removal of one electron in both the planar-like and buckled-like phases and re-analyze the high-resolution core-level XPS spectrum.

In this Letter, we follow the thrust of DFT that promises to give the total energy and CD of a many-body interacting system to study the core-level quasiparticles in silicene on $ZrB_2(0001)$ in both the planar-like and buckled-like forms without suffering from the

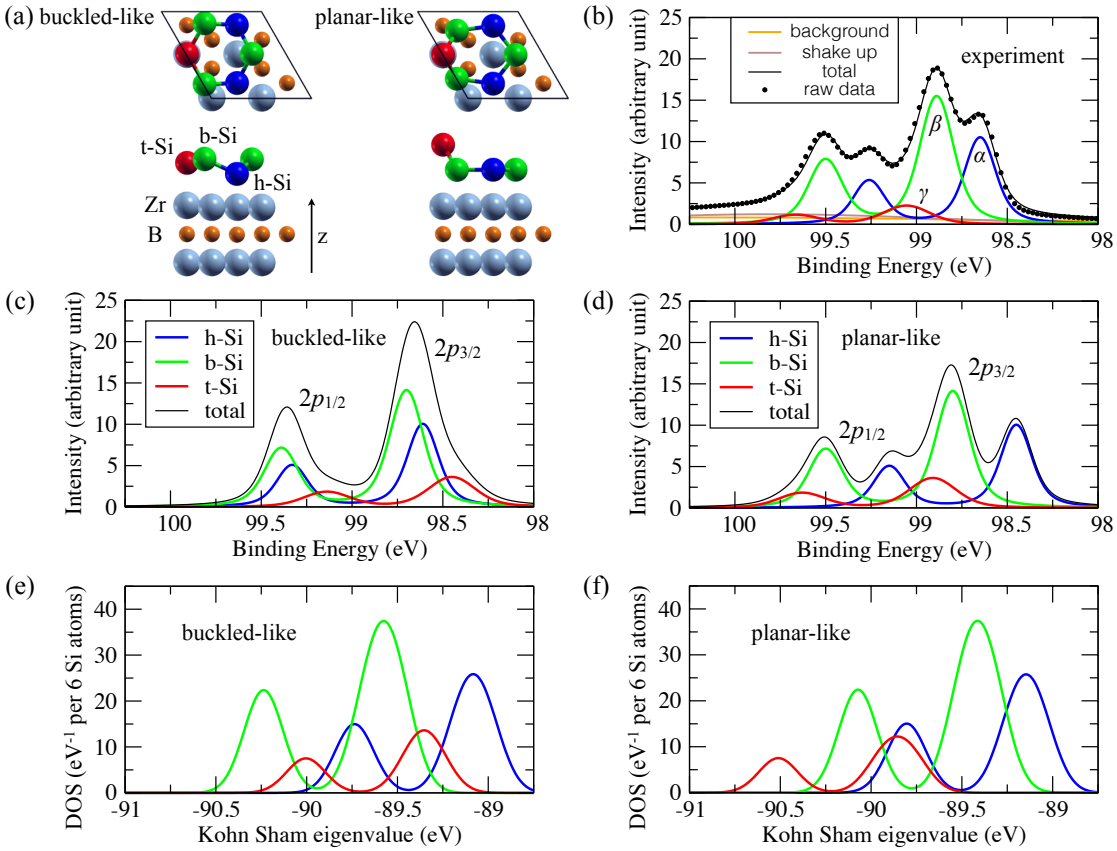

FIG. 1. (Color online). (a) Structures of buckled-like and planar-like silicene, where the t-Si (red), b-Si (green), and h-Si (blue) are indicated. (b) Measured Si $2p$ XPS spectrum (filled dots) and fitting results by symmetric Voigt functions. The fitted α (blue), β (green), and γ (red) peaks together with the background (orange) and shake-up (brown) contributions are presented. DFT-GGA binding energies are plotted by the same Voigt broadening using the energy listed in Table I, and the area ratio of h-Si, b-Si, and t-Si is considered as 2:3:1 for both of the (c) buckled-like and (d) planar-like silicene. Density of states of buckled-like and planar-like silicene with Gaussian broadening of 0.15 eV is shown in (e) and (f), respectively.

imposed periodic boundary condition. The core holes are found to be strongly dressed by other electrons, and the renormalized CD of such quasiholes can be directly visualized. The induced correlation is found to change the energy sequence of the quasiholes belonging to different Si atoms in comparison with that revealed in the DOS, and the binding energies are also distinguishable between the two model structures of silicene, allowing the verification by the XPS experiments.

The first-principles calculations were performed using the OpenMX code[35], where the addition of penalty functional for simulating creation of an atomic core hole and the exact Coulomb-cutoff technique for avoiding the undesired interaction between periodic holes were implemented[34]. Although the developments allow us revisiting the energies of quasiparticles beyond the knowledge of single-particle eigenvalues, the approximation to the exchange-correlation functional still plays a role that could alter the results. Here, we used the commonly adopted generalized gradient approximation[36] to study the total energy and CD. The norm-conserving relativistic pseudopotentials and optimized pseudo-atomic basis functions were also adopted as additional approximations to the all-electron problem[37–39]. The spin-orbit coupling was taken into account and responsible for the energy splitting between $j = 1/2$ and $j = 3/2$ angular momenta. Three, two, and two optimized radial functions were allocated for the s, p, and d orbitals for each Zr atom with a cutoff radius of 7 bohr, respectively, denoted as Zr7.0-$s3p2d2$. For Si and B atoms, Si7.0-$s2p2d1$ and B7.0-$s2p2d1$ were chosen. A cutoff energy of 220 Ry was used for numerical integrations and for the solution of the Poisson equation. The 2×2 k-point sampling was adopted for the (4×4) $ZrB_2(0001)$ unit cell whose in-plane lattice constant was set to 4×3.174 Å[25]. The slab with five Zr layers and four B layers were studied and terminated by either the Zr layer or silicene. The vacuum thickness separating the slabs was set to 20 Å.

The XPS measurements were performed using synchrotron radiation source at Photon Factory BL-13B (2015S2-008). The spectra were recorded by a hemispherical electron energy analyzer (Scienta SES200). All

the measurements were carried out at 300K in ultrahigh vacuum (UHV). The zero binding energy was taken at the Fermi edge of a tantalum foil attached to the sample holder. Normal emission spectra were collected. The incident photon energies were 260 eV. The ZrB_2 film was epitaxially grown on the Si(111) substrate by chemical vapor deposition in UHV at JAIST. An oxide- and contamination-free epitaxial silicene monolayer was prepared on the ZrB_2/Si(111) substrate by heating the sample at 1053K for about 30 minutes in UHV. The measured Si $2p$ spectrum (raw data) was fitted using symmetric Voigt functions for three Si atoms labelled as α, β, and γ and shake-up components[40] together with a Shirley-type background; note that asymmetric functions were adopted previously[23, 40].

The structures of planar-like and buckled-like phases, obtained by the DFT calculations, are presented in Fig. 1 (a). The buckled-like silicene resembles the freestanding silicene[41] but the lower Si atoms are pushed up while locating on top of Zr atoms, denoted as t-Si, in comparison with the other lower Si atoms locating above the centers of Zr triangles, denoted as hollow-Si (h-Si). The higher Si atoms are immune to further buckling and locate above the Zr-Zr bonds as bridging Zr atoms, denoted as b-Si. On the other hand, the planar-like silicene possesses a different structure, where only the t-Si is protruding out leaving the others at similar heights, close to a planar structure. The different structures should give distinguishable energies of core levels. Indeed, as shown in Figs. 1 (e) and (f), the DOS of the buckled-like and planar-like phases differs from each other prominently.

The physical picture of quasiparticle can be understood as a bare particle plus dressing particles. Once a Si $2p$ electron is removed from silicene as a bare hole, the surrounding electrons that were correlated with the removed electron would act on, for example, screening the positive charge of the hole in reducing the electrostatic energy and bring the system to a new state. The new state should be described by the many-body eigenstates of $N-1$ electrons. To have long lifetime for the renormalized hole, the best scenario is that the new state belongs to a single eigenstate $|m\rangle$. The energy of the quasihole can be considered as $E_{QH} = E_m^{N-1} - E_0^N$, where E_0 denotes the ground state. Obviously, if the quasihole is created, the system immediately falls into the eigenstate $|m\rangle$ with the total energy $E_0^N + E_{QH}$. After minimizing the total energy of the system with the bare hole, the DFT-proposed state is then considered as the excited state $|m\rangle$. In XPS experiments, the information of binding energy $E_B = \mu^N + E_{QH}$ is obtained, where μ denotes the chemical potential. For reaching good convergence of E_B against supercell sizes in metallic systems, the value can be determined by $E_B^{metal} = E_m^N - E_0^N$[34]. The E_B^{metal}'s of Si $2p$ orbitals calculated on the (4×4) $ZrB_2(0001)$ substrate and the convergence test of h-Si of the planar-like phase in collinear calculations as well as the observed XPS peaks are listed in Table I.

TABLE I. Binding energies (E_B^{metal}) of Si $2p_{1/2}$ and $2p_{3/2}$ orbitals of silicene on (4×4) $ZrB_2(0001)$ in the buckled-like (B-like) and planar-like (P-like) structures as well as the fitting values of XPS peaks in eV. E_B^{metal}'s of P-like h-Si $2p_z$ orbitals against supercell sizes from collinear calculations are also listed for examining the convergence. $n_{m,0}^N$ denotes $\int |n_m^N(\vec{r}) - n_0^N(\vec{r})| d\vec{r}$ in the unit of number of electrons.

(4×4)	$j = 1/2$			$j = 3/2$		
	h-Si	b-Si	t-Si	h-Si	b-Si	t-Si
B-like E_B^{metal}	99.33	99.39	99.14	98.61	98.70	98.45
$n_{m,0}^N$	3.15	3.09	3.03	3.18	3.12	3.08
P-like E_B^{metal}	99.15	99.50	99.63	98.45	98.80	98.91
$n_{m,0}^N$	3.07	3.03	3.13	3.12	3.07	3.16
exp	α	β	γ	α	β	γ
	99.26	99.50	99.67	98.65	98.89	99.05
P-like	(2×2)	(4×4)	(6×6)			
h-Si	98.43	98.35	98.37			

The XPS experiments and fitting results reveal three sets of peaks labelled as α, β, and γ contributed from three different Si atoms. Each set contains two peaks corresponding to the $2p_{1/2}$ and $2p_{3/2}$ contributions. As shown in Fig. 1 (b), the α and γ peaks have the smallest and largest binding energies, respectively, together with the in-between β peak in each j contribution. Interestingly, the DFT-revealed peaks for the $2p_{1/2}$ and $2p_{3/2}$ holes created in h-Si, b-Si, and t-Si of the planar-like phase shown in Fig. 1 (d) agree quite well with the α, β, and γ peaks, respectively, in the absolute scale. In contrast, the t-Si E_B^{metal} of the buckled-like phase possesses the smallest value as presented in Fig. 1 (c), which is inconsistent with the XPS measurements. This finding resolves the puzzling discrepancy in the core-level binding energies between experiments and those obtained from the ground-state planar-like phase.

Note that the previously reported XPS study compared the relative eigenvalues of Kohn-Sham orbitals of the buckled-like phase[23]. Regardless of about 9 eV deviation in the absolute values, the DOS of buckled-like phase resembles the XPS peaks fitted by asymmetric pseudo-Voigt functions[40], not the planar-like phase. Although it is expected that the use of symmetric Voigt functions should give the observed spectra if all the relevant sources, such as classical oscillators, are known, the fitted peaks using symmetric Voigt functions resemble the DOS of neither the buckled-like nor the planar-like silicene. Since the Si $2p$ core levels are localized in energy away from the other oscillators and the major energy splittings are the gaps between the $j = 1/2$ and $j = 3/2$ peaks, the relevant final states should be describable by the energy-minimized DFT states with the $2p_{1/2}$ and $2p_{3/2}$ core holes. As having been demonstrated, the calculated absolute values of E_B^{metal}'s of the planar-like phase beyond DOS are verified by the XPS experiments

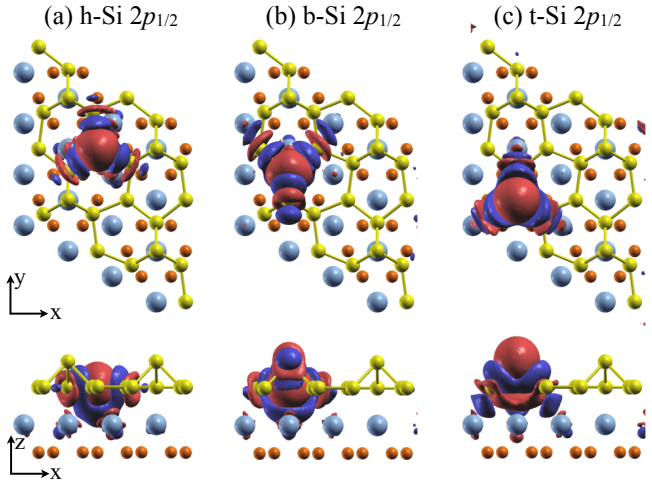

FIG. 2. (Color online). Charge density modification, defined as $n_m^N - n_0^N$, of planar-like silicene (yellow). The positive (red) and negative (blue) contributions indicate the amounts of charge density need to be added and removed from n_0^N, respectively. The charge-density surface is plotted at 0.001 $e/bohr^3$. The cases with core holes created in (a) h-Si $2p_{1/2}$, (b) b-Si $2p_{1/2}$, and (c) t-Si $2p_{1/2}$ are presented. The $2p_{3/2}$ results are similar to the $2p_{1/2}$ ones (not shown).

using unbiased fitting functions.

The strength of binding energies were commonly explained by the DOS. As shown in Figs. 1 (e) and (f), the energy sequence of core electrons in the buckled-like phase is b-Si, t-Si, and h-Si, where the b-Si eigenvalue has the lowest value, while the sequence is t-Si, b-Si, and h-Si in the planar-like phase. These relative eigenvalues can be understood in terms of the Coulomb repulsion between orbitals. Assuming the orbitals distribute their CD from each atomic center to its near neighbors, having more near neighbors would give stronger Coulomb repulsion and increase the energy. Each Si atom has three nearest neighbor Si atoms together with the nearest neighbor Zr atoms. Guided by the structures in Fig. 1 (a), the coordination numbers of t-Si, b-Si, and h-Si are considered as four, three, and six in the buckled-like phase and three, five, and six in the planar-like phase, respectively, which exactly map the energy sequences in the DOS.

However, the energy sequences encounter more modifications after considering the response of CD. The quasihole CD can be defined as $n_{QH} = n_m^{N-1} - n_0^N$. Unlike non-interacting electrons, the quasihole CD is not purely negative in real space so that both electrons and holes can be created. Therefore, the bare holes, such as occupied Kohn-Sham orbitals obtained in the N-electron system, cannot reflect the quasiparticle nature due to lack of description of positive quasihole CD. For metallic systems, n_{QH} is defined as $n_m^N - n_0^N + \delta n$, where δn can be considered as dilute electron gas. The integration of δn over the whole system should be -1. The major CD response to the bare hole can be focused on $n_m^N - n_0^N$, where the positive and negative values reflect the needed electron-hole pairs created in the ground state. Since the integration of $n_m^N - n_0^N$ over the whole system is zero, the integral $n_{m,0}^N \equiv \int |n_m^N(\vec{r}) - n_0^N(\vec{r})| d\vec{r}$ over the studied supercell quantifies the strength of the CD modification. As listed in Table I, $n_{m,0}^N$ is in order of three electrons that cannot be described by a single-particle eigenstate. This modification enhances the h-Si E_B^{metal} in the buckled-like phase and suppresses the t-Si E_B^{metal} in the planar-like phase in comparison with the respective DOS. As a result, the energy sequences of the peaks in both phases are changed, especially in the buckled-like phase. Although the relative values of the planar-like phase in the DOS are similar to those in the E_B^{metal}'s, having the modification gives the well separated $2p_{1/2}$ and $2p_{3/2}$ peaks that reach good agreement with the XPS measurements.

The quasihole CD can be visualized in real space. The n_{QH} of planar-like phase without presenting δn is plotted in Fig. 2. Importantly, both positive and negative contributions corresponding to the addition and removal of electrons from the ground state, respectively, can be identified. The spherical shape of positive CD surrounding the Si atom with a core hole can be seen in Fig. 2, which screens the positive charge. The deviation of each quasihole from the atomic eigenstate can also be recognized from the CD distribution that shows large values in the neighboring atoms, including the top-layer Zr atoms. This clearly supports that the created holes are strongly dressed by the electrons of surrounding atoms. The difference of n_{QH} between $2p_{1/2}$ and $2p_{3/2}$ states is responsible for giving the energy splitting due to spin-orbit coupling. At long distance from the core, there is no significant difference, for example, the 0.001 $e/bohr^3$ CD surface shown in Fig. 2, reflecting the electrostatic screening of a positive point charge. In a non-interacting system, there is no positive $n_{QH}(\vec{r})$ since creation of a core hole causes no response of the other electrons. Our study shows the importance of both signs of n_{QH} for delivering the accurate values of absolute binding energies.

In summary, the exact Coulomb-cutoff method allows us revisiting the picture of quasiparticles with creation of core holes from first principles. The core-level quasiholes in silicene on $ZrB_2(0001)$ have been studied following the content of DFT by calculating the many-body total energies and CD directly. From that, the addition and removal attributes of quashihole CD that cannot be revealed by a single-particle eigenstate are demonstrated. The puzzling discrepancy between the core-level spectra and the DOS revealed by Kohn-Sham orbitals of the ground-state planar-like phase has been resolved by comparing the binding energies in the absolute values without resorting to the single-particle eigenvalues. The core holes are found to be strongly dressed by other electrons evident from the large CD modifications involving surrounding atoms and the change in the energy sequence. The agreement of theory and experiment highlights the

success of DFT in fingerprinting the binding energies of the surface atoms including spin-orbit coupling. This work paves a way for future exploration of quasiparticles in various materials beyond perturbation theories.

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